

TO-92B



ECB

2SA1015 is PNP silicon planar transistor designed for audio frequency general purpose amplifier applications and driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	150mA
Total Power Dissipation	Ptot	400mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +125°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector Cutoff Current	ICBO		100	nA	VCB=50V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=5V IC=0
D.C. Current Gain	HFE	70 25	400		IC=2mA VCE=6V IC=150mA VCE=6V*
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=100mA IB=10mA*
Base-Emitter Saturation Voltage	VBE(sat)		1.1	V	IC=100mA IB=10mA*
Current Gain-Bandwidth Product	fT	80		MHz	IC=1mA VCE=10V
Output Capacitance	Cob		7	pF	VCB=10V f=1MHz
Noise Figure	NF		10	dB	IC=100µA VCB=6V Rg=10KΩ f=1KHz

* Pulse Test : Pulse Width = 300µs, Duty Cycle = 2%.

HFE Grouping @ IC=2mA VCE=6V

O : 70-140 Y : 120-240 GR : 200-400



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1-1. Dmp

This datasheet has been downloaded from:

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